

Semiconductor Device Modelling and Simulation
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Lecture-53
Problem Session-8

Hello, welcome to lecture number 53.

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PROBLEM-I CALCULATE SCATTERING RATE

Calculate scattering rate due to (a) static defect and (b) travelling wave

• Scattering rate due to i^{th} scattering event $\lambda_i = \frac{1}{\Gamma_i} \int S_i(k, k') dk'$

• Recall from lecture 38

$$S_i(k, k') = \frac{2\pi}{\hbar} |H(k, k')|^2 \delta(E' - E \mp \hbar\omega)$$

$$H(k, k') = \int \psi_i^* U_{i0}(\vec{r}) \psi d\vec{r}$$

$E' = E \pm \hbar\omega$
 $\Delta E = 0$ for a static scattering potential
 $\Delta E = \pm \hbar\omega$ for an oscillating scattering potential $U_{i0}(\vec{r}) = U_i e^{i(\omega t - \vec{k} \cdot \vec{r})}$

Handwritten notes: $N \rightarrow E, k \rightarrow E', k'$; $S(k, k') f(k) (1 - f(k'))$; $H(k, k') \rightarrow U_i$; $\delta(E' - E \mp \hbar\omega)$; $\psi_i^* U_{i0}(\vec{r}) \psi$

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In last class we discussed about the Monte Carlo simulation, now we will take up some problem related to Monte Carlo simulation. In Monte Carlo simulation we discussed that we started with n number of particles and we track them basically through certain scattering event. Energy E and the wave vector k, when it is scattered it has new energy E prime and wave vector k prime and then of course we track these particles and from their tracking we estimated what is there over all response to particular excitation.

Now as a first problem let us take or calculate the scattering rate due to defects. We will consider 2 defects here; one is static defect another defect which is traveling wave type. So, your static defect can be the ionized impurity scattering, traveling wave defect can be your phonon, acoustic phonon or optical phonon. Now let us recall this S k comma k prime is the scattering probability. And then we say the scattering rate from k to k prime is basically scattering probability

multiplied the probability of finding electron in k and then probability that there is a empty state in k' , so that is $1 - f(k')$.

And then of course we estimate that if we say this is basically full, this is empty you can just say $S(k, k')$. So, let us assume this is $S(k, k')$ then if we integrate it over all the k' , we will get the overall scattering rate for is state wave vector k . Now if you recall from lecture number 38, we discussed that a scattering probability $S(k, k')$ due to i th scattering event is given by $2\pi \times \hbar \times |U_{k, k'}|^2 \times \delta(E' - E \pm \hbar\omega)$.

This delta term here basically represents the conservation of energy, so that means your E' is final energy and which should be equal to E the initial energy $\pm \hbar\omega$. Here plus term indicate that there is absorption of some energetic particle with energy $\hbar\omega$ and minus means there is a emission of this particle. So, these particles are actually low energy like phonons and they have low energies.

So, change in energy of the electron is quite a small, so this delta term basically represents the energy conservation. Then $2\pi \times \hbar \times |U_{k, k'}|^2$, \hbar is the reduced Planck constant, so it is a constant term here. $U_{k, k'}$ is a matrix element due to the scattering potential let us call it U . So, some scattering potential due to the defect or phonon may be there, so this is a matrix element due to scattering potential and then it is calculated as the wave function of the final state.

So, that is basically corresponding with the k' times scattering potential times the wave function of the initial state and integrated over space. Another thing if you can note here for static scattering potential such as ionized impurity scattering, this change in energy 0. So, this is basically you can say it is an elastic scattering. For phonon scattering, so phonon basically involves the oscillation of these ions is basically, so due to this phonon scattering this is basically some kind of traveling wave is there, some kind of oscillation is there.

And these oscillations are quantized and their energy is given by some $n + \frac{1}{2} \hbar \omega$, where ω is the angular frequency of these phonons. So, the energy which is absorbed or released due to phonon scattering will be $\pm \hbar \omega$. And their scattering potential will be represented by some function with e to the power $\pm g \omega t$.

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SCATTERING POTENTIAL

$$S_i(k, k') = \frac{2\pi}{\hbar} |H(k, k')|^2 \delta(E' - E \mp \hbar\omega)$$

$$H(k, k') = \int \psi_f^* U_{s0}(\vec{r}) \psi_i d\vec{r}$$

- Scattering potential can be given as

$$U_{s0}(\vec{r}) = U^a(\vec{r})e^{-i\omega t} + U^e(\vec{r})e^{i\omega t}$$

- Electron wave function as product of envelop function and a periodic function (as per Bloch's theorem)

$$\psi_{nk}(\vec{r}) \approx G_n(\vec{r}, t) u_{nk}(\vec{r}) = e^{i\vec{k}\cdot\vec{r}} u_{nk}(\vec{r})$$

Handwritten notes on the slide:
 $\psi_{nk}(\vec{r}) = e^{i\vec{k}\cdot\vec{r}} u_{nk}(\vec{r})$
 $\psi_{nk'}(\vec{r}) = e^{i\vec{k}'\cdot\vec{r}} u_{nk'}(\vec{r})$

Now we have defined the scattering rate probability S_i , then this matrix element $H(k, k')$. Then scattering potential in general can be written as 2 components the absorbing condition or absorbing scattering potential and the scattering potential related to the emitting of these phonons. And when you substitute this scattering potential to calculate matrix element H , you have to substitute this wave function also initial and final state wave function.

And wave function for a n th state and wave vector k is given as a product of periodic function $u_{nk}(\vec{r})$ which is periodic in space and the periodicity of this function is same as the periodicity of the crystal multiplied by a plane wave. And so this can be written as $e^{i\vec{k}\cdot\vec{r}}$ which is equation of plane wave times this periodic potential $u_{nk}(\vec{r})$, so this is ψ_{nk} . Similarly you can write $\psi_{nk'}$ will be $e^{i\vec{k}'\cdot\vec{r}}$ times $u_{nk'}(\vec{r})$. And then when you substitute 1 and 2 into 3rd equation.

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SCATTERING POTENTIAL

Scattering potential $U_{s0}(\vec{r}) = U^a(r)e^{-i\omega t} + U^e(r)e^{i\omega t}$

Electron wave function $\psi_{nk}(\vec{r}) \approx G_n(\vec{r}, t)u_{nk}(\vec{r}) = e^{i\vec{k}\cdot\vec{r}}u_{nk}(\vec{r})$

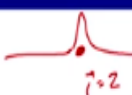
$H(k, k') = \int_V \psi_{nk'}^* U_{s0}(\vec{r}) \psi_{nk} d\vec{r} = \frac{1}{V} \int_V U_{s0}(\vec{r}) e^{-i(\vec{k}' - \vec{k})\cdot\vec{r}} d\vec{r}$ $\int_{U_{s0}(\vec{r})} U_{s0}(\vec{r})$

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So, this is substituted here, now this term $U_{nk}(\vec{r})$ times $U_{nk'}(\vec{r})$, this will give rise to this raise to normalized condition here and overall integral can be written as scattering potential U_{s0} times $e^{-i(\vec{k}' - \vec{k})\cdot\vec{r}}$ dr. So, this is basically because this is a complex conjugate, so it will come $e^{-i(\vec{k}' - \vec{k})\cdot\vec{r}}$ and this will be $e^{i\vec{k}\cdot\vec{r}}$. So, if you take them together it will be $e^{-i(\vec{k}' - \vec{k})\cdot\vec{r}}$, so this \vec{k}' is minus here and \vec{k} as plus so minus, minus, plus.

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PROBLEM-I(A) - DEFECT

Scattering potential $U_{s0}(\vec{r}) = A\delta(z)$ 

Electron wave function $\psi_{nk}(\vec{r}) \approx G_n(\vec{r}, t)u_{nk}(\vec{r}) = e^{i\vec{k}\cdot\vec{r}}u_{nk}(\vec{r})$

$H(k, k') = \frac{1}{L} \int_V U_{s0}(\vec{r}) e^{-i(\vec{k}' - \vec{k})\cdot\vec{r}} d\vec{r} = \frac{A}{L} \int_{-\infty}^{\infty} \delta(z) e^{i(k' - k)z} dz$

$S_r(k, k') = \frac{2\pi}{\hbar} |H(k, k')|^2 \delta(E' - E \mp \hbar\omega)$

$= \frac{2\pi}{\hbar} \left(\frac{A}{L}\right)^2 \delta(E' - E) \rightarrow \text{does not depend on } \omega$

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Now let us consider scattering potential due to a defect. Now defect as a nature, it is localized at particular position $r = z$, some position. So, you can say let us say it is some $x = 0$, $y = 0$ and $z =$

z at some position, so it is localized. So, its scattering potential can be approximated by some kind of delta function basically. So, in the vicinity of the defect let us say its influence is negligible and when it is at this defect it is basically very high potential basically.

So, you can say this $A \delta z$, then when you substitute this $A \delta z$ to calculate the matrix element H of k comma k' , so this will be $U_s 0$ times e to the power $i(k - k')r$. So, this is basically A can be taken out and this 1 by v (()) (09:27) because this is we are assuming 1 dimensional, so 1 by v will become 1 by L , so this is A by L times δz times e to the power $i(k - k')r$ dr or you can say $r z$ times dz that also can be done.

Now if you look at this function this is basically kind of Fourier transform for delta z function. And Fourier transform of delta is basically 1 , so it will be simply 1 basically, so you will have simply A by L . Then of course when you substitute this matrix element to calculate the scattering probability for scattering from k to k' there is 2π by \hbar matrix element square times delta.

Now in this case there is no traveling wave, so no $\hbar\omega$, so this is basically term is 0 , so it is simply $E - E'$. So, this is basically means energy is conserved and there is no change in the energy and the scattering is elastic. So, this scattering probability S_i will be 2π by \hbar A by L square times $\delta E' - E$. And here you notice one more thing it does not depend on k or k' . So, it is basically constant regardless of the wave vector.

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PROBLEM-I(B) – TRAVELLING WAVE

- Scattering potential $U_{s0}(\vec{r}) = Ae^{i(\beta z - \omega t)} = A e^{i(\vec{k}' \cdot \vec{r} - \omega t)}$
- Electron wave function $\psi_{nk}(\vec{r}) \approx G_n(\vec{r}, t) u_{nk}(\vec{r}) = e^{i\vec{k} \cdot \vec{r}} u_{nk}(\vec{r})$

$$H(k, k') = \int_V U_{s0}(\vec{r}) e^{-i(\vec{k}' - \vec{k}) \cdot \vec{r}} d\vec{r} = A e^{-i\omega t} \delta(k' - k - \beta)$$

$$S_i(k, k') = \frac{2\pi}{\hbar} |H(k, k')|^2 \delta(E' - E \mp \hbar\omega)$$

$$= \frac{2\pi}{\hbar} (A)^2 \delta(E' - E - \hbar\omega)$$

$E' = E \pm \hbar\omega$

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Similarly we can calculate the scattering probability due to traveling wave type of defects such as phonons. So, here we can represent the potential by e to the power $Iota B z - omega t$. And in general form it is basically A times e to the power $Iota$ then $beta \cdot r - omega t$. Now this $omega$ is basically the angular frequency of scattering potential and $beta$ is basically some kind of propagation constant.

Now again if you substitute these electron wave functions to calculate this matrix element H of k comma k prime. Here you will get A can be taken out and this is e to the power $Iota beta z - omega t$ times e to the power $Iota k - k$ prime r dr . So, all these $Iotas$ can be basically combined and $omega t$ can be taken out because we are integrating with respect to position. So, $A e$ to the power $- Iota omega t$ can be taken out and in the integral we have e to the power $Iota k - k$ prime $+ beta$.

Let us write this also as r . So, that is let us use this general expression A this is r times dr . Now integral of this exponential function is basically is a delta function basically. Of course there is a 1 by v is also, there is a 1 by volume is also there, so delta function. So, that means your A times e to the power $-Iota omega t$ times delta of $k - k$ prime $+ beta$. So, if you compare here that means k prime $= k + beta$.

So, there is a conservation of momentum basically because the momentum is $\hbar k$, so $\hbar k' = \hbar k + \hbar \beta$. And because this k has changed and it is a $e^{-i\omega t}$ also, so there will be change in energy also. So, when you substitute this matrix element to calculate the probability of scattering, so 2π by \hbar matrix element square times $\delta(E - E' - \hbar\omega)$.

And this is basically the magnitude of matrix element here, so the matrix element this magnitude will be simply A . Because $e^{-i\omega t}$ magnitude is 1 basically, so it will be $2\pi \hbar A^2 \delta(E - E' - \hbar\omega)$ because there is a minus sign here, so this is $-\hbar\omega$ is coming here. So, that way we can calculate for a given scattering potential or given a scattering type, we can calculate these scattering probabilities.

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RELAXATION TIME

Scattering rate
 $\frac{1}{\tau_c} = \lambda_1 = \frac{1}{\Gamma_1} = \int_{\Gamma_2} S_1(k, k') (1 - f(k')) dk'$

Momentum relaxation time
 $\frac{1}{\tau_{M1}} = \lambda_1 = \frac{1}{\Gamma_1} = \int_{\Gamma_2} S_1(k, k') \left(1 - \frac{k'}{k}\right) dk'$
Handwritten notes: $\frac{\hbar k - \hbar k'}{\hbar k} = 1 - \frac{k'}{k}$ | $\frac{1}{\tau_{M1}} = \frac{1}{\tau_c} \left(1 - \frac{k'}{k}\right)$ | $\frac{1}{\tau_{M1}} > \frac{1}{\tau_c}$

Energy relaxation time
 $\frac{1}{\tau_{E1}} = \lambda_1 = \frac{1}{\Gamma_1} = \int_{\Gamma_2} S_1(k, k') \left(1 - \frac{E(k')}{E(k)}\right) dk'$
Handwritten notes: $\frac{E(k) - E(k')}{E(k)} = 1 - \frac{E(k')}{E(k)}$ | $\frac{1}{\tau_{E1}} = \frac{1}{\tau_c} \left(1 - \frac{E(k')}{E(k)}\right)$ | $\frac{1}{\tau_{E1}} > \frac{1}{\tau_c}$

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And once we have this scattering probabilities we can find out what is the scattering rate. So, that is basically integral $S dk$ of course into f into $1 - f$ of k' all those can be included. And then if you want to calculate the momentum reduction rate then this scattering probability can be multiplied with the change in momentum. Now change in momentum is $\hbar k - \hbar k'$ divided by $\hbar k$.

So, \hbar will cancel out and you will have basically $1 - k'$ by k , so this factor is coming here, so that will be the momentum relaxation rate. Similarly energy relaxation rate, so it will be $E_k - E_{k'}$ the change in energy ΔE divided by E_k , so then of course you can write it as $1 - E_{k'}$ by E_k , so you can calculate the energy relaxation rate. Now generally this relaxation rates are different from the scattering rates because not all the scattering events are causing the change in energy or causing the change in momentum.

There are some scattering which are isotropic, so they are basically altering the momentum to the maximum they are contributing to the momentum relaxation rate and which are not isotropic. Their contribution to the change in moment of relaxation it is small, so this is basically momentum relaxation time. So, this will be you can write 1 by τ let us call it τ_m , this we call it 1 over τ_E and let us call it 1 over τ .

So, τ_m will be more than τ as far as energy relaxation time is concerned there are some scattering which are elastic. So, for them this ΔE is 0 , there are some which are non elastic or inelastic, for them there is a change in energy. So, that means this τ_E will also be more than τ . So, these are the different relaxation times that can be calculated from the calculated value of this scattering probabilities.

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PROBLEM-2 SCATTERING

The probability of an electron suffering a collision in any infinitesimal interval dt is just dt/τ . $\frac{1}{\tau}$ - scattering rate

(a) Show that an electron picked at random at a given moment had no collision during the preceding t seconds with probability $e^{-t/\tau}$. Show that it will have no collision during the next t seconds with the same probability.

Handwritten derivation:

$$\lim_{N \rightarrow \infty} \left(1 - \frac{dt}{\tau}\right)^N = \lim_{N \rightarrow \infty} e^{N \ln\left(1 - \frac{dt}{\tau}\right)}$$

$$= e^{\lim_{N \rightarrow \infty} N \ln\left(1 - \frac{dt}{\tau}\right)}$$

$$= e^{-\frac{t}{\tau}}$$

Another derivation:

$$\lim_{N \rightarrow \infty} \frac{1 - \left(1 - \frac{dt}{\tau}\right)^N}{\frac{dt}{\tau}} = \frac{t}{\tau}$$

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Now let us consider another problem with whose result actually we used in discussing Monte Carlo simulation. Let us consider that the probability of an electrons suffering the collision in any infinitesimal interval dt is just dt by τ , where 1 by τ is the scattering rate or you can say scattering probability. So, within dt by dt time the scattering probability is dt by τ . Now we have to show that electron picked up at random at a given moment had no collision during the preceding t seconds with probability e to the power $-t$ by τ .

That means if you start at $t = 0$ or at $t = 0$ then you go till time t . Then in this period what is the probability that a particular electron does not have a collision? And that probability is e to the power $-t$ by τ that we have to prove. So, we know that scattering rate is 1 by τ and scattering probability is 1 by τ and in time duration dt scattering probability is dt by τ , so what we can do?

We can break this region 0 to t into n number of parts, so we can consider very small parts basically. And that let us call it dt there are n number of part, so from $t = 0$ next is t by n , the next is $2t$ by n and so on. So, during this small period t by n probability of a scattering is dt by τ , so the probability of a scattering is dt is t by N divided by τ . And probability of not scattering is $1 - t$ by n that is dt by τ .

Similarly in the next interval which is also t by n because from t by n to $2t$ by n , so same probability is there for next cycle, for third interval, fourth interval and so on. So, that means for n intervals this probability will be $1 - t$ by n τ to the power n . So, that is a probability that electron did not have a collision from 0 to t , now what we have to do? We can assume that this N goes to infinity or that means this t by n goes to 0 , so we have to evaluate this from limit N tending to infinity and what will be this?

We can write this one in the form limit N tending to infinity $1 - t$ by n τ to the power n . So, it can be written as exponential N log of $1 - t$ by N τ because e to the power log is basically same number. And by using the properties of this limit we can write this is e to the power limit N tending to infinity log of $1 - t$ by n τ divided by this n can written as 1 by n here. Now we have some numerator by denominator and if you recall there is a L hospital rule.

You can take the derivative of numerator and denominator, so if you take the derivative, so this denominator derivative is $1/n^2$ because d/dn of $1/n$ is N^{-2} , so $-1/n^2$. And this log term is $1/(1-t/\tau)$ multiplied by $\log x$ is $1/x$ and this is $1-c$, so derivative is 0 and this will be t/τ times N^2 . And then if you put limit N tending to infinity, so this is $1/N^2$ $1/N^2$ these 2 will basically cancel, that is different colours, this N^2 , this N^2 will cancel.

And this N goes to infinity, t is finite, so this will be 0 basically, so this will be simply t/τ and with a minus sign, this is a minus sign here. So, it can be written as $e^{-t/\tau}$ and that is what we have to prove. So, that means for the time 0 to t the probability that electron will not have collision is $e^{-t/\tau}$. And that is the reason we chose this exponential function while discussing the Monte Carlo simulation. So, we approximated this thing with exponential function.

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PROBLEM-2 SCATTERING

The probability of an electron suffering a collision in any infinitesimal interval dt is just dt/τ .

(a) Show that an electron picked at random at a given moment had no collision during the preceding t seconds with probability $e^{-t/\tau}$. Show that it will have no collision during the next t seconds with the same probability.

(b) Show that the probability that the time interval between two successive collisions of an electron falls in the range between t and $t + dt$ is $(dt/\tau) e^{-t/\tau}$.

$e^{-t/\tau} \cdot \frac{dt}{\tau}$

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Now, so that the probability that the time interval between 2 successive collisions of an electron falls in the range between t and $t + dt$ is dt/τ times $e^{-t/\tau}$. So, that means you start with $t = 0$ and consider up to t until time t there is no collision. So, there is a first collision here at $t = t$, then second collision is between $t + dt$, so there is another collision in between these 2 regions.

So, what is the probability? That there is no collisions up to t that is $e^{-t/\tau}$, so this is a probability of first collision at time t . Now between this time interval dt , there is another collision. So, this first collision at t which is $e^{-t/\tau}$, so there are 2 successive collisions. So, first collision probability is $e^{-t/\tau}$, so that means there is no collision till t , there is a collision at t , so that is $e^{-t/\tau}$.

Then there is another collision if you start at t , so between t and $t+dt$ there is another collision and its probability is dt/τ . So, overall probability is basically the product of these 2 probabilities and that is what is shown here through the b part. So, this result also we used in discussing the Monte Carlo simulation.

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PROBLEM-2 SCATTERING

The probability of an electron suffering a collision in any infinitesimal interval dt is just dt/τ .

(a) Show that an electron picked at random at a given moment had no collision during the preceding t seconds with probability $e^{-t/\tau}$. Show that it will have no collision during the next t seconds with the same probability.

(b) Show that the probability that the time interval between two successive collisions of an electron falls in the range between t and $t + dt$ is $(dt/\tau) e^{-t/\tau}$.

(c) Show as a consequence of (a) that at any moment the mean time back to the last collision (or up to the next collision) averaged over all electrons is τ .

Handwritten notes for (b): $n_0 dt = n_0 \tau \frac{dt}{\tau} \Rightarrow \ln n_0 = \ln n_0 - t/\tau$

Handwritten notes for (c): $\langle t \rangle = \frac{\int_0^\infty t \cdot \frac{dt}{\tau} e^{-t/\tau} dt}{\int_0^\infty \frac{dt}{\tau} e^{-t/\tau} dt} = \frac{\int_0^\infty t e^{-t/\tau} dt}{\int_0^\infty e^{-t/\tau} dt} = \frac{1}{\tau} \int_0^\infty t e^{-t/\tau} dt = \frac{1}{\tau} \left[-\tau t e^{-t/\tau} - \int -\tau e^{-t/\tau} dt \right]_0^\infty = \frac{1}{\tau} \left[-\tau t e^{-t/\tau} + \tau e^{-t/\tau} \right]_0^\infty = \frac{1}{\tau} \left[0 - 0 - (-\tau) \right] = \tau$

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Then as a consequence of a that at any moment the mean time back to the last collision or up to the next collision averaged over all electron is τ , that you have to prove. So, this average time can be calculated as $\int t \cdot dn$ divided by $\int dn$, so this t is the time for a collision. Then we can use this expression for N we know that the probability of collision is dt/τ , that is the probability of collision.

So, that means this is the probability of change in the number of electrons which have gone through the collision. So, you can write this as dn by n , so number of electrons that have collided

but this is basically if there are n naught electrons at $t = 0$, let us say there are n naught electron at $t = 0$ which I have not gone through the collision. So, at next time this number will decrease basically.

So, let us say Δn or dn have gone through the collision, so now electron which I have not gone through the collision will be $n - \Delta n$. So, this dt by τ will basically change the ion, so you can write $-dn$ by n is dt by τ . And if you use this one, so if you integrate let us say from n_0 to n and this is let us say 0 to t , so you will get \log of n by n naught minus sign = t by τ and from this you can write $n = n$ naught exponential $-t$ by τ .

So, this is the relationship how the electron which have not gone through the collision changes with time. So, from this you can write $dn = n$ naught $e^{-t/\tau}$ times $-dt$ by τ and that you can substitute here, times t and it can be integrated. So, this dn let us say n naught to 0 , this is 0 to some time t , this also has a dn , so you can write n naught to 0 here basically. So, when you integrate it this will be n naught here.

So, this n naught and this naught can be taken out, so this will in terms of dt , so what you will have here t times $e^{-t/\tau}$ then dt . And τ can be taken out and n naught will cancel out, so this will be 1 over τ and this is 0 to certain limit to infinity basically. Because at infinite time none of the electron is remaining which has not gone through the collision, so that means all the electrons have gone through the collision.

So, this can be integrated using integrations by parts, so if you recall that there is integral $U dv$ it can be written as $U v - \int v du$. So, this is let us say u and this is v , so this can be written as u is t and integral this thing will be $e^{-t/\tau}$ divided by -1 by τ . And this is $-du$ is 1 and dv is $e^{-t/\tau}$ divided by -1 by τ times dt and this is the limit 0 to infinity, this is limit 0 to infinity.

So, at $t = 0$ this is multiplied by t , so this will be 0 as infinite $e^{-t/\tau}$, so this will basically be 0 . And this will be τ can be taken out, so this will be τ and the integral $e^{-t/\tau}$ will be -1 by τ , so minus sign here 0 to infinity. So, at infinity this is 0 , at 0 this

is 1 by τ , so it becomes basically τ square, so τ square by τ will be τ . So, that has basically proves that time back to the last collision averaged over all electron is actually τ .

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So, that is all for today. So, in this lecture we have discussed problem related to scattering rate and the calculation of probabilities. In next session we will begin our discussion about quantum transport, thank you very much.